











SN74LVC1G3157-Q1

SCES463F - JUNE 2003-REVISED MARCH 2015

SN74LVC1G3157-Q1 Single-Pole Double-Throw Analog Switch

Features

- **Qualified for Automotive Applications**
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- 1.65-V to 5.5-V V_{CC} Operation
- Useful for Analog and Digital Applications
- Specified Break-Before-Make Switching
- Rail-to-Rail Signal Handling
- High Degree of Linearity
- High Speed, Typically 0.5 ns $(V_{CC} = 3 \text{ V}, C_{L} = 50 \text{ pF})$
- Low ON-State Resistance, Typically ≉6 Ω $(V_{CC} = 4.5 \text{ V})$
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II

2 Applications

Advanced Driver Assistance Systems (ADAS)

3 Description

The SN74LVC1G3157-Q1 device is a single-pole double-throw (SPDT) analog switch designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC1G3157 device can handle analog and digital signals. The device permits signals with amplitudes of up to V_{CC} (peak) to be transmitted in either direction.

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
CN741 VC1C2157 O1	SOT-23 (6)	2.90 mm × 1.60 mm
SN74LVC1G3157-Q1	SC70 (6)	2.00 mm x 1.25 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Logic Diagram (Positive Logic)

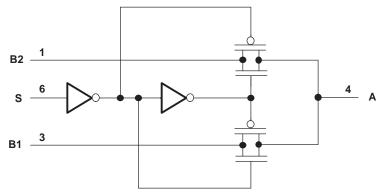




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4 Revision History

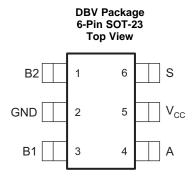
Changes from Revision E (April 2008) to Revision F

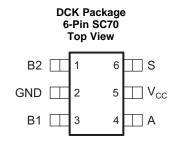
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Added ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section



5 Pin Configuration and Functions





See mechanical drawings for dimensions.

Pin Functions

PIN		1/0	DESCRIPTION
NO.	NAME	I/O	DESCRIPTION
1	B2	I/O	Second terminal
2	GND	_	Ground
3	B1	I/O	First terminal
4	Α	I/O	Common terminal
5	VCC	I	Power supply
6	S	I	Select



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage ⁽²⁾	-0.5	6.5	V	
V_{IN}	Control input voltage ⁽²⁾⁽³⁾	-0.5	6.5	V	
$V_{I/O}$	/ _{I/O} Switch I/O voltage ⁽²⁾⁽³⁾⁽⁴⁾⁽⁵⁾				V
I _{IK}	Control input clamp current	V _{IN} < 0	-50		mA
I _{IOK}	I/O port diode current	V _{I/O} < 0	-50		mA
I _{I/O}	ON-state switch current	$V_{I/O} = 0 \text{ to } V_{CC}^{(6)}$		±128	mA
	Continuous current through V _{CC} or GND			±100	mA
Δ	Package thermal impedance ⁽⁷⁾	DBV package		165	°C/W
θ_{JA}	rackage memai impedance**/	DCK package		258	C/VV
T _{stg}	Storage temperature		-65	150	°C

Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

All voltages are with respect to ground, unless otherwise specified.

This value is limited to 5.5 V maximum.

(6)

6.2 ESD Ratings

	VALUE	UNIT
Human body model (HBM), performed per JEDEC (JESD22)	±2000	
V _(ESD) Electrostatic discharge Charged device model (CDM), Other pins	±1000	V
performed per JEDEC (JESD22) Corner pins (B2, B1, S, and A)	±1000	

The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

 $[\]rm V_{I},\,\rm V_{O},\,\rm V_{A},$ and $\rm V_{Bn}$ are used to denote specific conditions for $\rm V_{I/O}.$ (5)

 $I_{\rm I}, I_{\rm O}, I_{\rm A}$, and $I_{\rm Bn}$ are used to denote specific conditions for $I_{\rm I/O}$. The package thermal impedance is calculated in accordance with JESD 51-7.



6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	NOM MAX	UNIT
V _{CC}			1.65	5.5	V
V _{I/O}			0	V _{CC}	V
V _{IN}			0	5.5	V
M. I Park Invest	igh lovel input voltage control input	V _{CC} = 1.65 V to 1.95 V	V _{CC} × 0.75		V
V _{IH} Hi	High-level input voltage, control input	$V_{CC} = 2.3 \text{ V to } 5.5 \text{ V}$	$V_{CC} \times 0.7$		V
V Land land Secret rate as a sector Count	our lovel input voltage, control input	V _{CC} = 1.65 V to 1.95 V		$V_{CC} \times 0.25$	V
V _{IL} Lo	Low-level input voltage, control input	$V_{CC} = 2.3 \text{ V to } 5.5 \text{ V}$		$V_{CC} \times 0.3$	V
		V _{CC} = 1.65 V to 1.95 V		20	
Λ4/Λ I	and the critical vice (fall times	V _{CC} = 2.3 V to 2.7 V		20	//
Δt/Δv In	Input transition rise/fall time	V _{CC} = 3 V to 3.6 V		10	ns/V
		V _{CC} = 4.5 V to 5.5 V		10	
T _A		,	-40	125	°C

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, SCBA004.

6.4 Thermal Information

		SN74LVC1	SN74LVC1G3157-Q1			
	THERMAL METRIC ⁽¹⁾	DBV (SOT-23)	DCK (SC70)	UNIT		
		6 PINS	6 PINS			
$R_{\theta JA}$	Junction-to-ambient thermal resistance	201.8	233.8			
R ₀ JC(top)	Junction-to-case (top) thermal resistance	103.7	107.9			
$R_{\theta JB}$	Junction-to-board thermal resistance	51.8	52.7	°C/W		
ΨЈТ	Junction-to-top characterization parameter	12	4.9			
ΨЈВ	Junction-to-board characterization parameter	51.4	52.4			

⁽¹⁾ For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.



6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER		TES	T CONDITIONS		V _{cc}	MIN TYP ⁽¹⁾	MAX	UNIT
				$V_I = 0 V$,	I _O = 4 mA	4.05.1/	11	20	
				V _I = 1.65 V,	$I_O = -4 \text{ mA}$	1.65 V	15	50	
				$V_I = 0 V$,	I _O = 8 mA	0.0.1/	8	12	
				V _I = 2.3 V,	$I_O = -8 \text{ mA}$	2.3 V	11	30	
r _{on}	ON-state switch resistance	e ⁽²⁾	See Figure 2 and Figure 1	$V_I = 0 V$,	$I_O = 24 \text{ mA}$	3 V	7	9.5	Ω
			and rigure :	$V_I = 3 V$,	$I_O = -24 \text{ mA}$	3 V	9	20	
				$V_I = 0 V$,	$I_O = 30 \text{ mA}$		6	7.5	
				$V_1 = 2.4 V$,	$I_O = -30 \text{ mA}$	4.5 V	7	12	
				$V_1 = 4.5$,	$I_{O} = -30 \text{ mA}$		7	15	
					$I_A = -4 \text{ mA}$	1.65 V		140	
r	ON-state switch resistance	e	$0 \le V_{Bn} \le V_{CC}$		$I_A = -8 \text{ mA}$	2.3 V		45	Ω
r _{range}	over signal range ⁽²⁾⁽³⁾		(see Figure 2 and F	Figure 1)	$I_A = -24 \text{ mA}$	3 V		18	32
					$I_A = -30 \text{ mA}$	4.5 V		10	
				$V_{Bn} = 1.15 V,$	$I_A = -4 \text{ mA}$	1.65 V	0.5		
۸۳	Difference in on-state resistance between		Soo Figure 2	$V_{Bn} = 1.6 V,$	$I_A = -8 \text{ mA}$	2.3 V	0.1		Ω
∆r _{on}	switches (2)(4)(5)	switches (2)(4)(5)	See Figure 2	$V_{Bn} = 2.1 V$,	$I_A = -24 \text{ mA}$	3 V	0.1		12
				$V_{Bn} = 3.15 V,$	$I_A = -30 \text{ mA}$	4.5 V	0.1		
			$I_A = -4 \text{ mA}$		$I_A = -4 \text{ mA}$	1.65 V	110		
_	ON-state resistance		0 < 1/ < 1/		$I_A = -8 \text{ mA}$	2.3 V	26		0
r _{on(flat)}	flatness (2) (4) (6)		$0 \le V_{Bn} \le V_{CC}$ $I_A = -24 \text{ mA}$ $I_A = -30 \text{ mA}$		$I_A = -24 \text{ mA}$	3 V	9		Ω
					4.5 V	4			
I _{off} ⁽⁷⁾	OFF-state switch leakage		0 < 1/ 1/ < 1/ (50	o Figuro 3)		1.65 V		±1	
off`	current		$0 \le V_I, V_O \le V_{CC}$ (se	e rigure 3)		to 5.5 V	±0.05	±1 ⁽¹⁾	μA
	ON state quitab leekage	ourront	$V_I = V_{CC}$ or GND, V	- Open (200 F	iguro 4)	5.5 V		±1	μA
I _{S(on)}	ON-state switch leakage	current	VI = VCC OI GIND, V	o = Open (see F	rigure 4)	5.5 V		±0.1 ⁽¹⁾	μΑ
	Control input ourrant		061/ 61/			0 V		±1	
I _{IN}	Control input current		$0 \le V_{IN} \le V_{CC}$		to 5.5 V	±0.05	±1 ⁽¹⁾	μA	
I _{CC}	Supply current		$V_{IN} = V_{CC}$ or GND			5.5 V	1	10	μΑ
ΔI_{CC}	Supply-current change		$V_{IN} = V_{CC} - 0.6 V$			5.5 V		500	μΑ
C _{in}	Control input capacitance	s				5 V	2.7		pF
C _{io(off)}	Switch I/O capacitance	Bn				5 V	5.2		pF
	Switch I/O consoitenes	Bn				5 V	17.3		
C _{io(on)}	Switch I/O capacitance	Α				οV	17.3		pF

⁽¹⁾ $T_A = 25^{\circ}C$

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Measured by the voltage drop between I/O pins at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages on the two (A or B) ports.

Specified by design

 $[\]Delta r_{on} = r_{on(max)} - r_{on(min)} \ \text{measured at identical V}_{CC}, \ \text{temperature, and voltage levels}$ This parameter is characterized, but not tested in production. (4)

Flatness is defined as the difference between the maximum and minimum values of ON-state resistance over the specified range of conditions.

 I_{off} is the same as $I_{\text{S(off)}}$ (OFF-state switch leakage current).



6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 5 and Figure 11)

PARAMETER	FROM	TO (OUTPUT)	V _{CC} = 1 ± 0.1	1.8 V 5 V	V _{CC} = 0.2	2.5 V 2 V	V _{CC} = ± 0.3		V _{CC} = ± 0.5	5 V 5 V	UNIT
	(INPUT)	(OUTPUT)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd} ⁽¹⁾	A or Bn	Bn or A		2		1.2		8.0		0.3	ns
t _{en} (2)	c	Bn	7	24	3.5	14	2.5	7.6	1.7	5.7	20
t _{dis} (3)	- S	Bu	3	13	2	7.5	1.5	5.3	0.8	3.8	ns
t _{B-M} ⁽⁴⁾			0.5		0.5		0.5		0.5		ns

⁽¹⁾ t_{pd} is the slower of t_{PLH} or t_{PHL} . Propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance when driven by an ideal voltage source (zero output impedance).

6.7 Analog Switch Characteristics

 $T_A = 25^{\circ}C$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V _{CC}	TYP	UNIT
				1.65 V	300	
Frequency response	A or Do	Do or A	$R_L = 50 \Omega$,	2.3 V	300	MHz
Frequency response (switch on) ⁽¹⁾	A or Bn	Bn or A	f _{in} = sine wave (see Figure 6)	3 V	300	IVIMZ
				4.5 V	300	
				1.65 V	-54	
Crosstalk	D4 or D2	B2 or B1	$R_L = 50 \Omega$,	2.3 V	-54	dB
(between switches) ⁽²⁾	B1 or B2		f _{in} = 10 MHz (sine wave) (see Figure 7)	3 V	-54	
				4.5 V	-54	
	A or Bn	Bn or A	C_L = 5 pF, R_L = 50 Ω , f_{in} = 10 MHz (sine wave) (see Figure 8)	1.65 V	– 57	dB
Feedthrough attenuation				2.3 V	– 57	
(switch off) ⁽²⁾				3 V	– 57	
				4.5 V	– 57	
Channa iniantian (3)		٨	$C_L = 0.1 \text{ nF}, R_L = 1 \text{ M}\Omega$	3.3 V	3	
Charge injection ⁽³⁾	S	Α	(see Figure 9)	5 V	7	pC
Total because its distant			V 0.5.Vm n D 600.O	1.65%	0.1%	
		Bn or A	V_I = 0.5 Vp-p, R_L = 600 Ω, f_{in} = 600 Hz to 20 kHz	2.3%	0.025%	V
Total harmonic distortion	A or Bn		(sine wave)	3%	0.015%	
			(see Figure 10)	4.5%	0.01%	

⁽¹⁾ Adjust f_{in} voltage to obtain 0 dBm at output. Increase f_{in} frequency until dB meter reads -3 dB.

⁽²⁾ t_{en} is the slower of t_{PZL} or t_{PZH}.

t_{dis} is the slower of t_{PLZ} or t_{PHZ}.

⁽⁴⁾ Specified by design

⁽²⁾ Adjust fin voltage to obtain 0 dBm at input.

⁽³⁾ Specified by design

6.8 Typical Characteristics

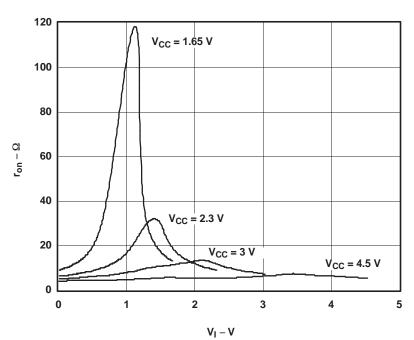


Figure 1. Typical R_{on} as a Function of Input Voltage (V_I) for $V_{I} = 0$ To V_{CC}

7 Parameter Measurement Information

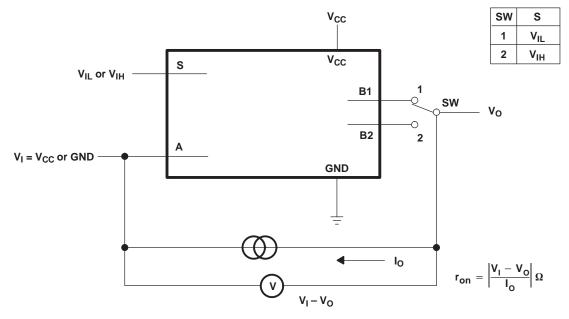
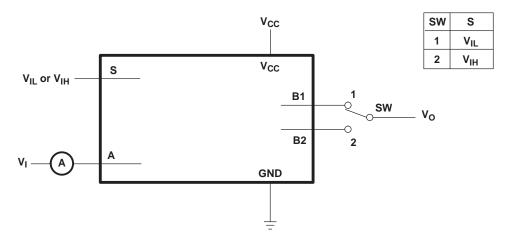


Figure 2. ON-State Resistance Test Circuit

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 $\begin{array}{l} \text{Condition 1: V}_I = \text{GND, V}_O = \text{V}_{CC} \\ \text{Condition 2: V}_I = \text{V}_{CC}, \text{V}_O = \text{GND} \\ \end{array}$

Figure 3. OFF-State Switch Leakage-Current Test Circuit

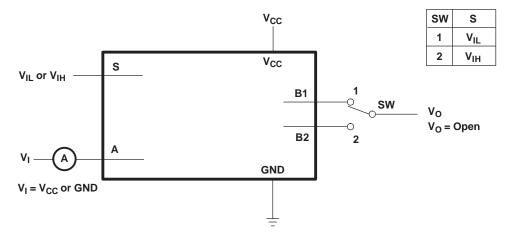
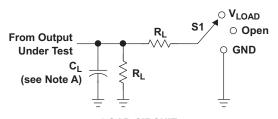


Figure 4. ON-State Switch Leakage-Current Test Circuit

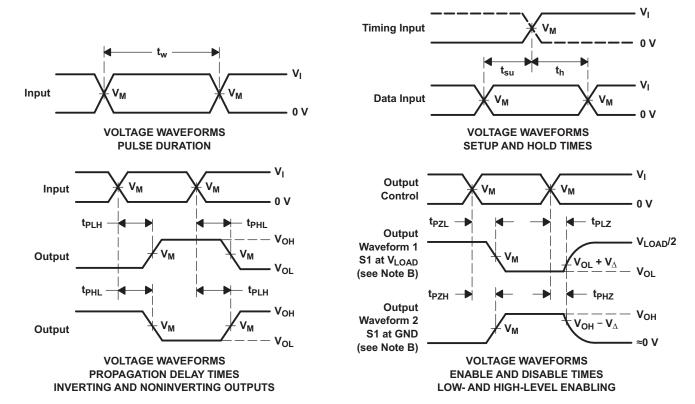




TEST	S 1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LOAD		\sim 1	ИΤ
LUAL	CIR	CU	111

v	INF	PUTS	.,	.,		_	.,	
V _{CC}	v _{CC} V _I		V _M	V _{LOAD}	CL	R _L	$V_{\!\Delta}$	
1.8 V ± 0.15 V	V _{CC}	≤2 ns	V _{CC} /2	2 × V _{CC}	50 pF	500 Ω	0.3 V	
2.5 V \pm 0.2 V	V _{CC}	≤2 ns	V _{CC} /2	2 × V _{CC}	50 pF	500 Ω	0.3 V	
3.3 V \pm 0.3 V	V _{CC}	≤2.5 ns	V _{CC} /2	2 × V _{CC}	50 pF	500 Ω	0.3 V	
5 V \pm 0.5 V	V _{CC}	≤2.5 ns	V _{CC} /2	2 × V _{CC}	50 pF	500 Ω	0.3 V	



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10-MHz, Z_O = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 5. Load Circuit and Voltage Waveforms

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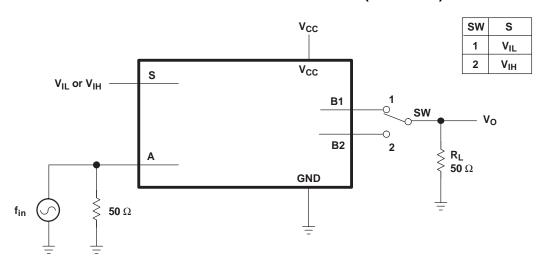


Figure 6. Frequency Response (Switch On)

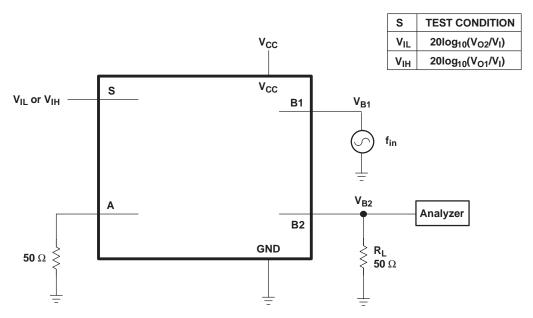


Figure 7. Crosstalk (Between Switches)

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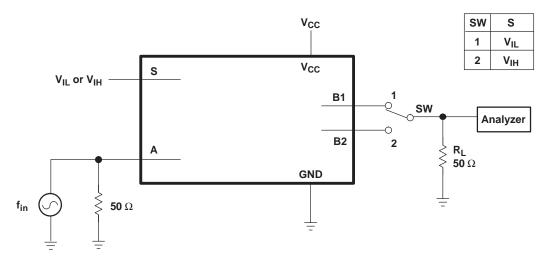


Figure 8. Feedthrough

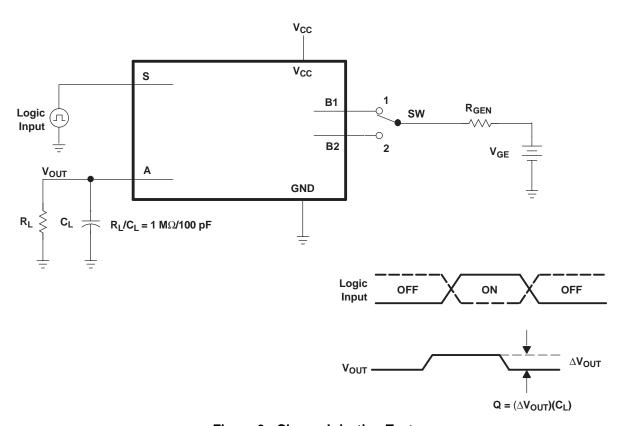


Figure 9. Charge-Injection Test

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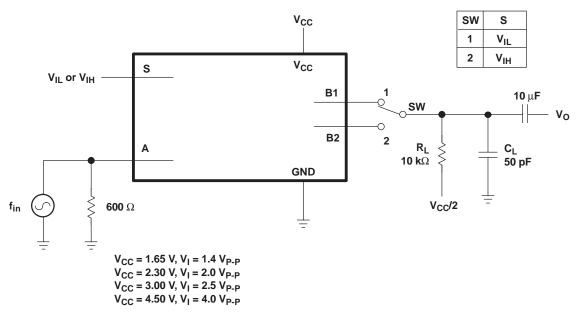


Figure 10. Total Harmonic Distortion

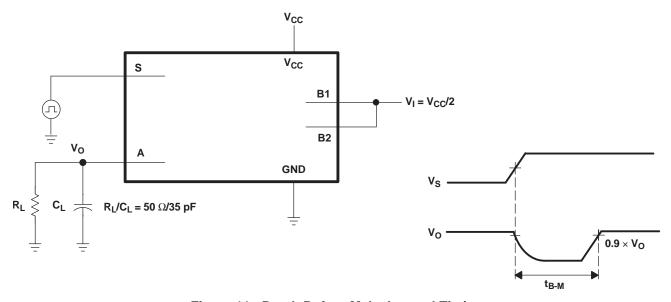


Figure 11. Break-Before-Make Internal Timing

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8 Detailed Description

8.1 Overview

The SN74LVC1G3157-Q1 device is a single-pole double-throw (SPDT) analog switch designed for 1.65-V to 5.5-

 V_{CC} operation. The SN74LVC1G3157-Q1 device can handle analog and digital signals. The device permits signals with amplitudes of up to V_{CC} (peak) to be transmitted in either direction.

8.2 Functional Block Diagram

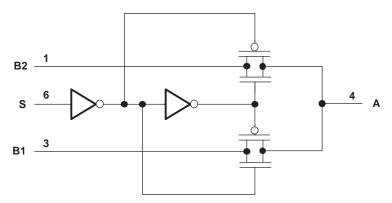


Figure 12. Logic Diagram (Positive Logic)

8.3 Feature Description

These devices are qualified for automotive applications. The 1.65-V to 5.5-V supply operation allows the device to function in many different systems comprised of different logic levels, allowing rail-to-rail signal switching. Either the B1 channel or the B2 channel is activated depending upon the control input. If the control input is low, B1 channel is selected. If the control input is high, B2 channel is selected.

8.4 Device Functional Modes

Table 1 lists the ON channel when one of the control inputs is selected.

Table 1. Function Table

CONTROL INPUTS	ON CHANNEL
L	B1
Н	B2



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74LVC1G3157-Q1 SPDT analog switch is flexible enough for use in a variety of circuits such as analog audio routing, power-up monitor, memory sharing and so on. For details on the applications, you can also view SCYB014.

9.2 Typical Application

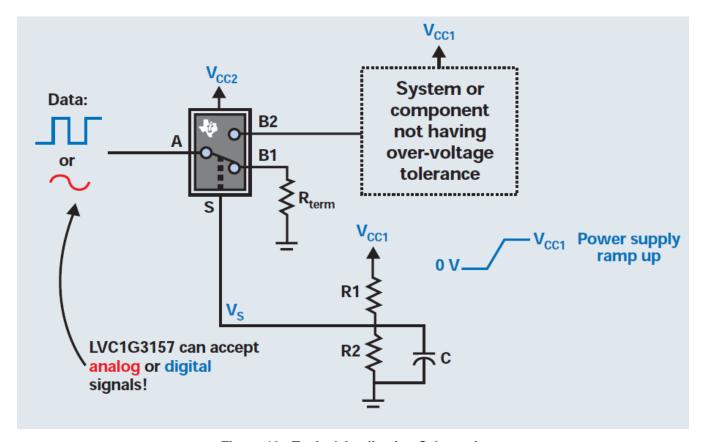


Figure 13. Typical Application Schematic

9.2.1 Design Requirements

The inputs can be analog or digital, but TI recommends waiting until VCC has ramped to a level in *Recommended Operating Conditions* before applying any signals. Appropriate termination resistors should be used depending on the type of signal and specification. The Select pin should not be left floating; either pull up or pull down with a resistor that can be overdriven by a GPIO.



Typical Application (continued)

9.2.2 Detailed Design Procedure

Using this circuit idea, a system designer can ensure a component or subsystem power has ramped up before allowing signals to be applied to its input. This is useful for integrated circuits that do not have overvoltage tolerant inputs. The basic idea uses a resistor divider on the VCC1 power rail, which is ramping up. The RC time constant of the resistor divider further delays the voltage ramp on the select pin of the SPDT bus switch. By carefully selecting values for R1, R2 and C, it is possible to ensure that VCC1 will reach its nominal value before the path from A to B2 is established, thus preventing a signal being present on an I/O before the device/system is powered up. To ensure the minimum desired delay is achieved, the designer should use Equation 1 to calculate the time required from a transition from ground (0 V) to half the supply voltage (VCC1/2).

$$Set\left(\frac{R2}{R1+R2} \times Vcc1 > VIH\right) of the select pin$$
(1)

Choose Rs and C to achieve the desired delay.

When Vs goes high, the signal will be passed.

9.2.3 Application Curve

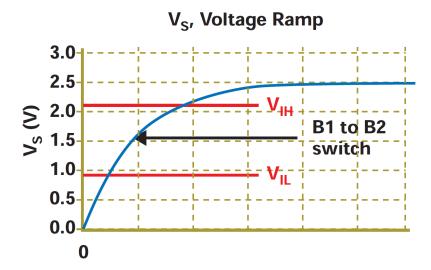


Figure 14. V_S Voltage Ramp

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10 Power Supply Recommendations

Most systems have a common 3.3-V or 5-V rail that can supply the V_{CC} pin of this device. If this is not available, a Switch-Mode-Power-Supply (SMPS) or a Linear Dropout Regulator (LDO) can be used to provide supply to this device from another voltage rail.

11 Layout

11.1 Layout Guidelines

TI recommends keeping signal lines as short as possible. TI also recommends incorporating microstrip or stripline techniques when signal lines are greater than 1 inch in length. These traces must be designed with a characteristic impedance of either 50 Ω or 75 Ω , as required by the application. Do not place this device too close to high-voltage switching components, as they may interfere with the device.

11.2 Layout Example

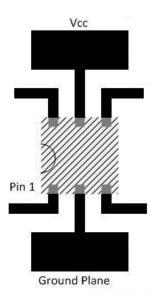


Figure 15. Recommended Layout Example



12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

SN74LVC1G3157 and SN74LVC2G53 SPDT Analog Switches, SCYB014

12.2 Trademarks

All trademarks are the property of their respective owners.

12.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.4 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGE OPTION ADDENDUM

31-Oct-2014

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
1P1G3157QDBVRQ1	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	CC5O	Samples
1P1G3157QDCKRQ1	ACTIVE	SC70	DCK	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C5O	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

31-Oct-2014

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LVC1G3157-Q1:

• Catalog: SN74LVC1G3157

NOTE: Qualified Version Definitions:

• Catalog - TI's standard catalog product

PACKAGE MATERIALS INFORMATION

www.ti.com 31-Oct-2014

TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
1P1G3157QDBVRQ1	SOT-23	DBV	6	3000	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
1P1G3157QDCKRQ1	SC70	DCK	6	3000	179.0	8.4	2.2	2.5	1.2	4.0	8.0	Q3

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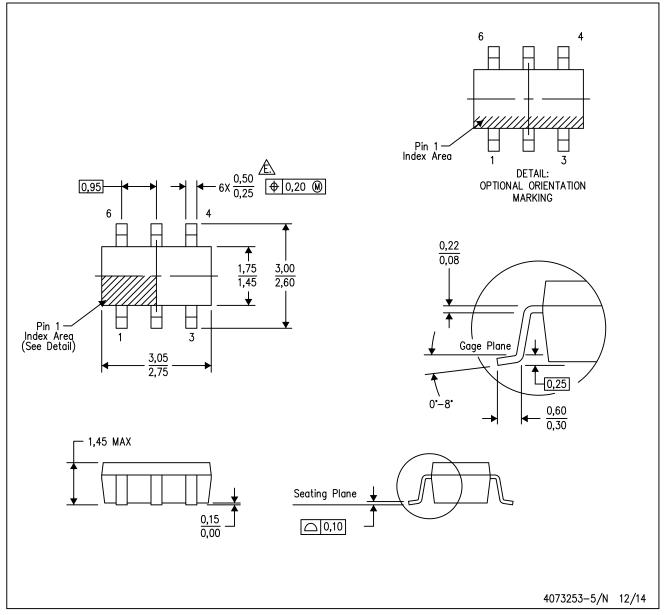


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
1P1G3157QDBVRQ1	SOT-23	DBV	6	3000	203.0	203.0	35.0
1P1G3157QDCKRQ1	SC70	DCK	6	3000	203.0	203.0	35.0

DBV (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE



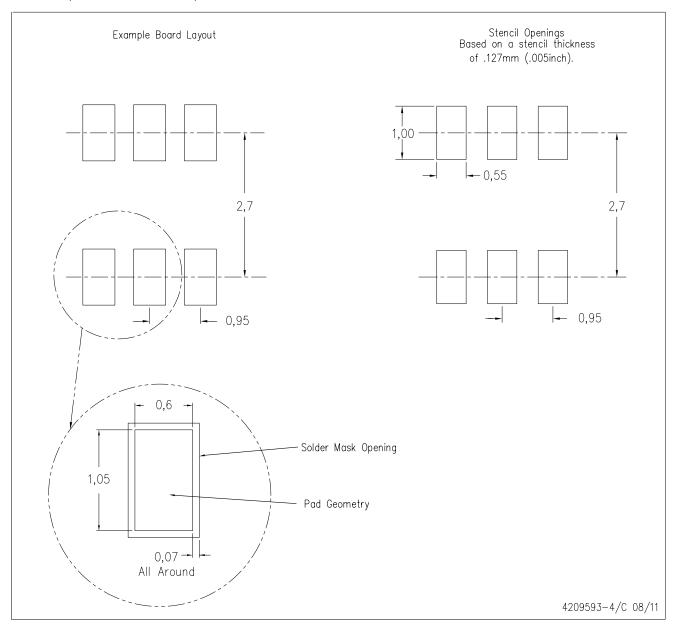
NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- Falls within JEDEC MO-178 Variation AB, except minimum lead width.



DBV (R-PDSO-G6)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



DCK (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AB.



DCK (R-PDSO-G6)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



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